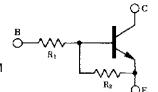


# COMPOUND TRANSISTOR AA1L3M

## on-chip resistor NPN silicon epitaxial transistor For mid-speed switching

#### **FEATURES**

• On-chip bias resistor  $(R_1 = 4.7 \; k\Omega, \; R_2 = 4.7 \; k\Omega)$ 



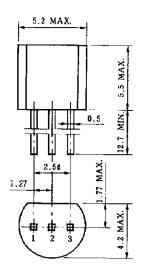
· Complementary transistor with AN1L3M

#### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vcво	60	V
Collector to emitter voltage	VCEO	50	V
Emitter to base voltage	VEBO	10	V
Collector current (DC)	Ic(DC)	100	mA
Collector current (Pulse)	Ic(pulse) *	200	mA
Total power dissipation	Рт	250	mW
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

<sup>\*</sup> PW  $\leq$  10 ms, duty cycle  $\leq$  50 %

#### PACKAGE DRAWING (UNIT: mm)



Electrode Connection

1. Emitter EIAJ : SC-43B
2. Collector JEDEC: TO-92
3. Base IEC : PA33

#### **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

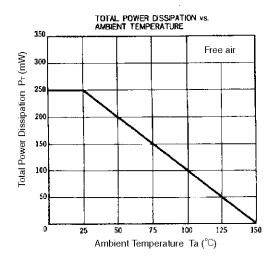
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0			100	nA
DC current gain	h <sub>FE1</sub> **	VcE = 5.0 V, Ic = 5.0 mA	20	40	80	-
DC current gain	h <sub>FE2</sub> **	VcE = 5.0 V, Ic = 50 mA	70	140		-
Collector saturation voltage	V <sub>CE(sat)</sub> **	Ic = 5.0 mA, Iв = 0.25 mA		0.08	0.3	V
Low level input voltage	VIL **	$V_{CE} = 5.0 \text{ V}, \text{ Ic} = 100 \ \mu\text{A}$		1.1	0.8	V
High level input voltage	V <sub>IH</sub> **	VcE = 0.2 V, Ic = 5.0 mA	3.0	1.5		V
Input resistance	R <sub>1</sub>		3.28	4.7	6.11	kΩ
Resistance ratio	R <sub>1</sub> /R <sub>2</sub>		0.9	1.0	1.1	-
Turn-on time	ton	$Vcc = 5 \text{ V}, \text{ RL} = 1 \text{ k}\Omega$			0.5	μs
Storage time	<b>t</b> stg	V <sub>I</sub> = 5 V, PW = 2 μs			3.0	μs
Turn-off time	toff	duty cycle≤2 %			5.0	μs

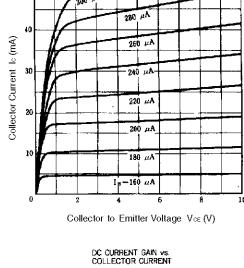
<sup>\*\*</sup> Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2 %

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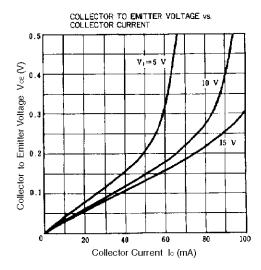
### TYPICAL CHARACTERISTICS (Ta = 25°C)

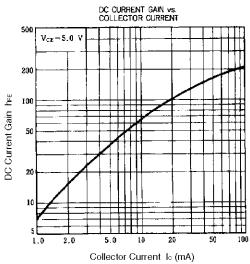


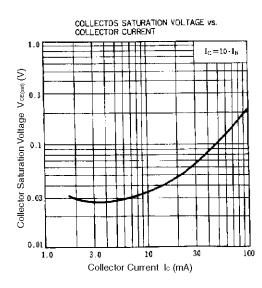


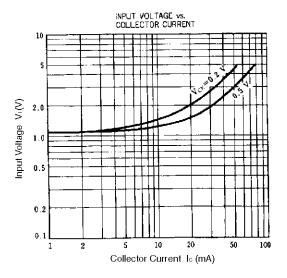
COLLECTOR CURRENT Vs. COLLECTOR TO EMITTER VOLTAGE

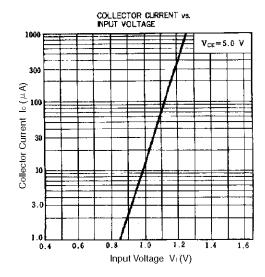
50

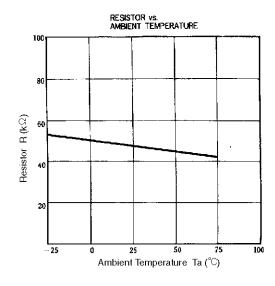












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